

AMENDMENTS TO THE SPECIFICATION

Please amend the Title of the Invention as follows:

~~METAL MESH FILTER COMPRISING SEMICONDUCTOR IMAGE~~
SENSOR AN IMAGE SENSOR, AN IMAGE SENSOR PIXEL, AND METHODS OF
FORMING THE SAME

Please replace paragraph [0003] beginning on page 2 with the following paragraph [0003].

[0003] The illustrated imager shown in FIG. 1 includes a conventional pixel cell 100. Pixel cell 100 typically includes a photodiode 4 having a p-region 8 and an n-region 6 in a p-substrate 2. The pixel 100 also includes a transfer transistor with associated gate 20, a floating diffusion region 16 formed in a more heavily doped p-type well 12, and a reset transistor with associated gate 18. Photons striking the surface of the p-region 8 of the photodiode 4 generate electrons that are collected in the n-region 6. From n-region 6, the accumulated charge is read out through circuitry comprising plugs 24 and conductive features 26 formed in successive transparent insulating layers 28 according to the desired characteristics of pixel cell 100. Pixel cell 100 further comprises trench isolation regions 10 formed in p-substrate 2 used to isolate adjacent pixel cells. A color filter 30 is typically formed on top of CMOS pixel 100 and substantially over photodiode 4. A microlens 32 may be provided over color filter 30 to direct incident light towards photodiode 4.